



175°C 60V DUAL P-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

Product Summary

BV _{DSS}	RDS(ON) Max	I _D T _C = +25°C
-60V	$48mΩ @ V_{GS} = -10V$	-26A
	60mΩ @ V _{GS} = -4.5V	-23A

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

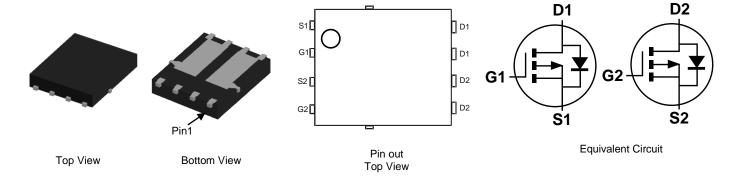
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Features

- Rated to +175°C ideal for high ambient temperature environments
- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Low R_{DS(ON)} minimises power losses
- Low Qg minimises switching losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMPH6050SPDQ</u>)

Mechanical Data

- Case: PowerDI5060-8 (Type C)
- Case Material: Molded Plastic, "Green" Molding Compound.
 - UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.097 grams (Approximate)



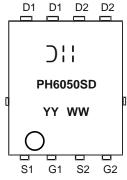
Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH6050SPD-13	PowerDI5060-8 (Type C)	2500 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



);; = Manufacturer's Marking
PH6050SD = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	-60	V		
Gate-Source Voltage	V_{GSS}	±20	V		
Continuous Drain Current (Note 6) V _{GS} = -10V	I _D	-6.3 -4.4	А		
Continuous Drain Current (Note 7) $V_{GS} = -10V$ Steady $T_C = +25^{\circ}C$ State $T_C = +100^{\circ}C$			I _D	-26 -18	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-40	Α		
Maximum Continuous Body Diode Forward Current (Note 6)	IS	-2.0	Α		
Avalanche Current (Note 8) L = 0.1mH	I _{AS}	-21	Α		
Avalanche Energy (Note 8) L = 0.1mH	E _{AS}	30	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.5	W
Thormal Posistance Junction to Ambient (Note 5)	Steady state	D.	100	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{ hetaJA}$	53	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	D	52	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	27	
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	2.9		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

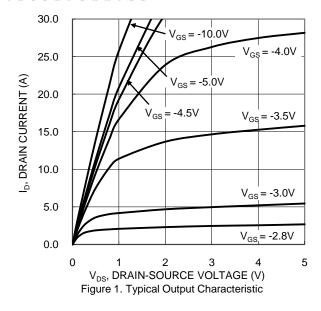
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

.							
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0		-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	D		36	48	mΩ	$V_{GS} = -10V, I_D = -5A$	
Static Dialif-Source Off-Resistance	R _{DS(ON)}	_	44	60	11122	$V_{GS} = -4.5V, I_{D} = -4A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V$, $I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	1525	_	pF), 20),), 0),	
Output Capacitance	Coss	_	90	_	pF	$V_{DS} = -30V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		70	_	pF	1 = 1.0WHZ	
Gate Resistance	Rg	_	16	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_{g}	_	14.5	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	30.6	_	nC	Vps = -30V. Ip = -5A	
Gate-Source Charge	Q_{gs}	_	4.9	_	nC	VDS = -30V, ID = -3A	
Gate-Drain Charge	Q_{gd}	_	5.2	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	5.3	_	ns		
Turn-On Rise Time	t _R	_	15.4	_	ns	$V_{GS} = -10V, V_{DS} = -30V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	79.2	_	ns	$R_G = 3\Omega$, $I_D = -5A$	
Turn-Off Fall Time	t _F	_	45.3	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	15.2	_	ns	I _F = -5A, di/dt = -100A/µs	
Body Diode Reverse Recovery Charge	Q _{RR}	_	9.3	_	nC	I _F = -5A, di/dt = -100A/μs	

Notes:

- $5.\ Device\ mounted\ on\ FR-4\ PC\ board,\ with\ minimum\ recommended\ pad\ layout,\ single\ sided.$
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.





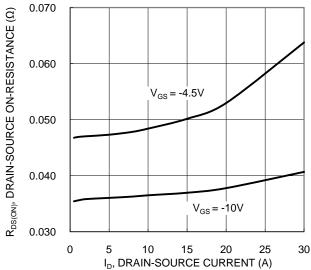


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

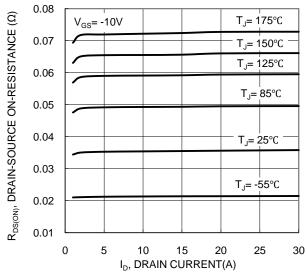


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

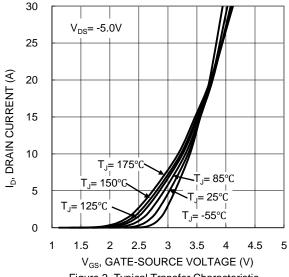
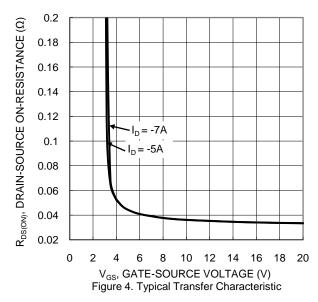


Figure 2. Typical Transfer Characteristic



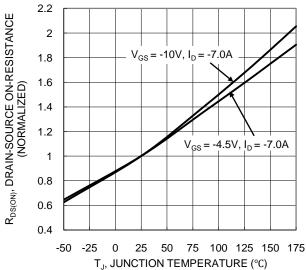


Figure 6. On-Resistance Variation with Temperature





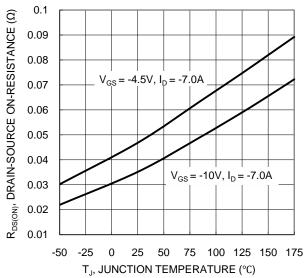
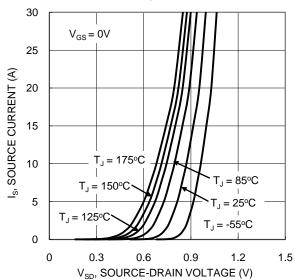
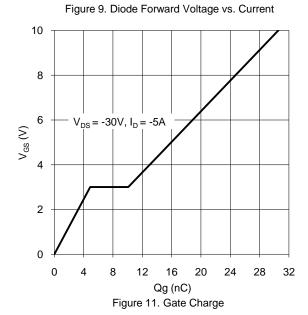


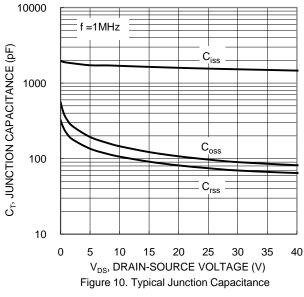
Figure 7. On-Resistance Variation with Temperature

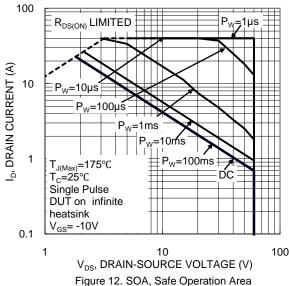




2.4 $V_{\text{GS(TH)}},$ GATE THRESHOLD VOLTAGE (V) 2.2 2 $I_D = -1mA$ 1.8 1.6 $I_D = -250 \mu A$ 1.4 1.2 1 8.0 -25 0 25 50 75 100 125 150 175 -50 T_.I, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs Temperature







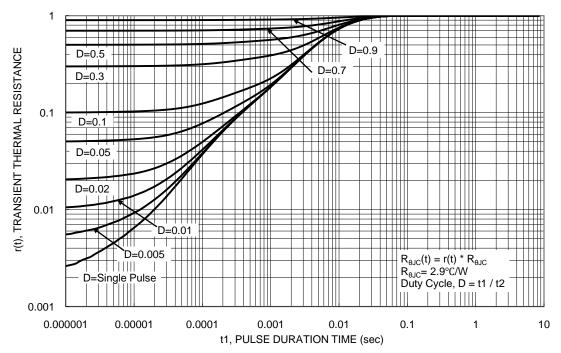


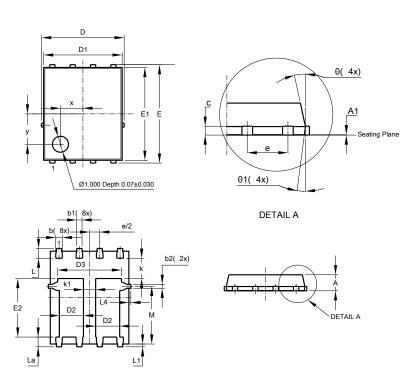
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type C)

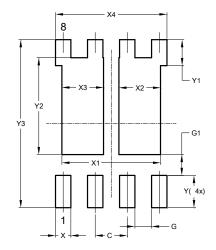


PowerDI5060-8 (Type C)					
Dim	Min Max		Тур		
Α	0.90	1.10	1.00		
A1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	5	.15 BS0	0		
D1	4.85	4.95	4.90		
D2	1.40	1.60	1.50		
D3	-	-	3.98		
Е	6.15 BSC				
E1	5.75	5.85	5.80		
E2	3.56	3.76	3.66		
е	1.27BSC				
k	1	-	1.27		
k1	0.56	-	-		
L	0.51	0.71	0.61		
La	0.51	0.71	0.61		
L1	0.05	0.20	0.175		
L4	1	-	0.125		
М	3.50	3.71	3.605		
X	-	-	1.400		
у	•	-	1.900		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type C)



Dimensions	Value		
	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	3.910		
X2	1.650		
Х3	1.650		
X4	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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